

Silicon NPN Power Transistors

2SC3300

DESCRIPTION

- With TO-3PN package
- Low saturation voltage
- Wide area of safe operation

APPLICATIONS

- Power and general purpose application

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

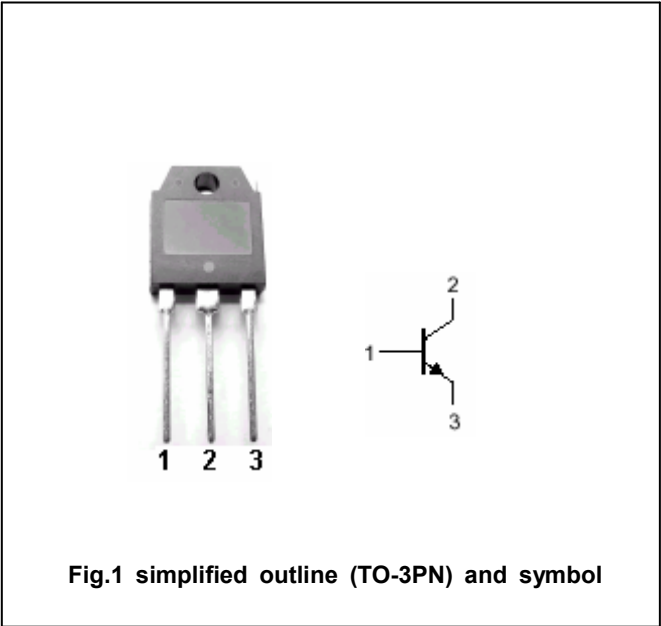


Fig.1 simplified outline (TO-3PN) and symbol

ABSOLUTE MAXIMUM RATINGS (TC=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	100	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current (DC)		15	A
I_{CM}	Collector current-peak		25	A
P_C	Collector power dissipation	$T_C=25^{\circ}C$	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA ; I_B=0$	100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1mA ; I_E=0$	100			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA ; I_C=0$	6			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C=10A ; I_B=1A$			0.5	V
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C=10A ; I_B=1A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=100V ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=6V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	$I_C=5A ; V_{CE}=4V$	30		120	

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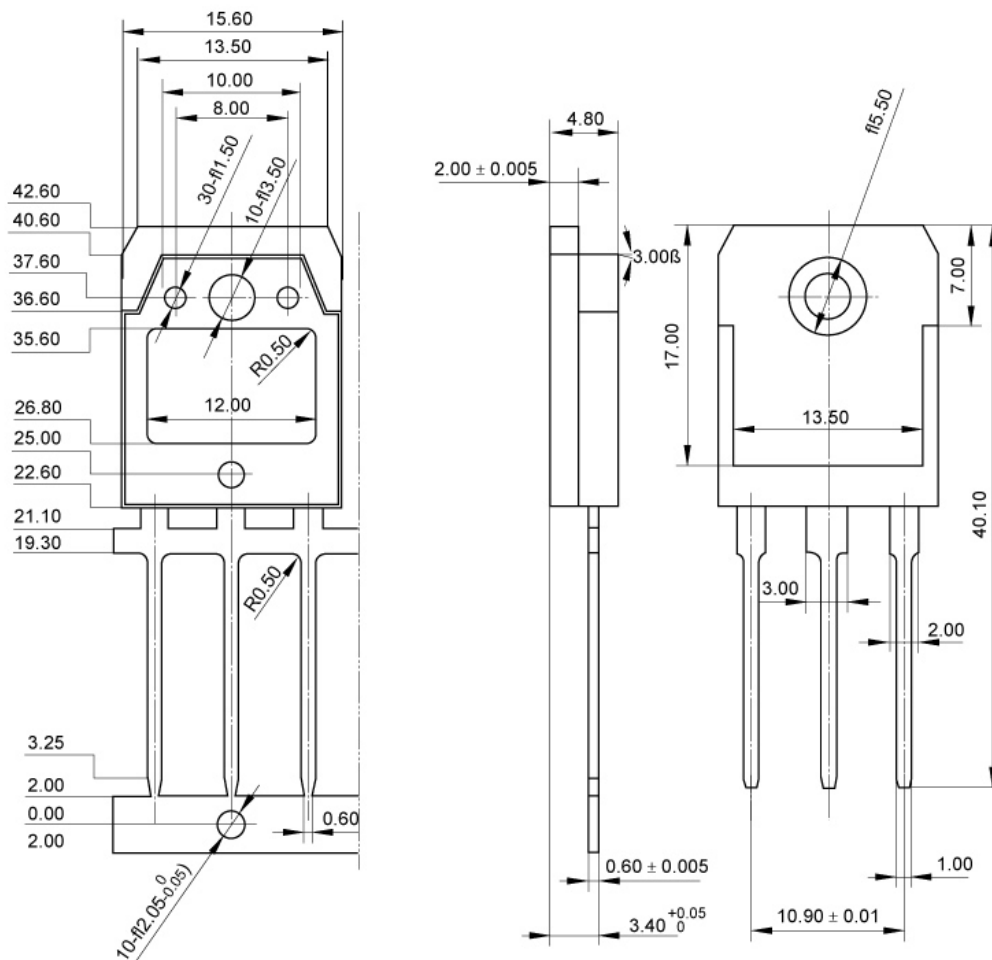


Fig.2 outline dimensions